Central™
Semiconductor Corp.

PROCESS CPD73

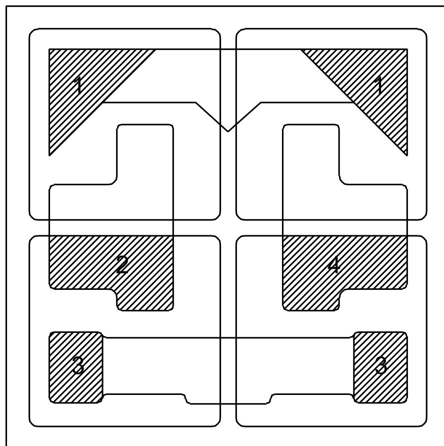
Bridge Rectifier

Monolithic Quad Diode Bridge Chip

PROCESS DETAILS

Die Size	25 x 25 MILS
Die Thickness	6.0 MILS
Bonding Pad Area 1 (+DC)	3.0 x 3.0 MILS
Bonding Pad Area 2 (AC)	3.0 x 7.0 MILS
Bonding Pad Area 3 (-DC)	3.0 x 4.0 MILS
Bonding Pad Area 4 (AC)	3.0 x 7.0 MILS
Top Side Metalization	Al - 12,000Å
Back Side Metalization	Au - 5,000Å

GEOMETRY



R1

GROSS DIE PER 3 INCH WAFER
10,000

PRINCIPAL DEVICE TYPES
CMFBR-6F

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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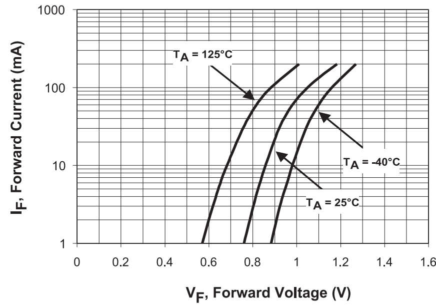
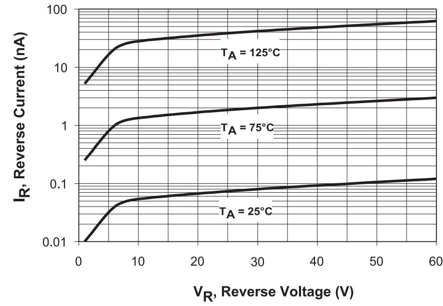
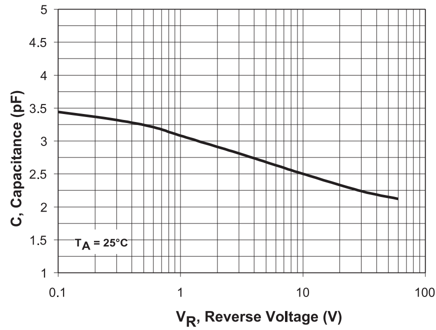
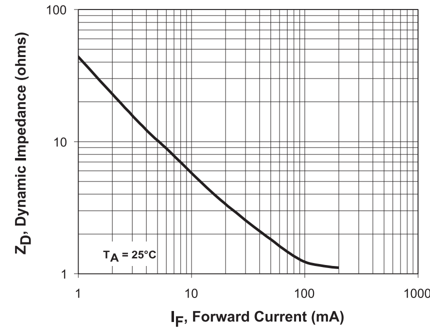
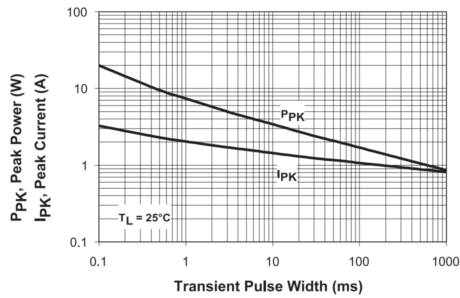
Typical Electrical Characteristics

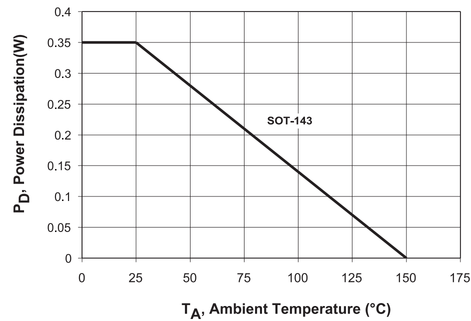












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